

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Previously Presented) A semiconductor device comprising:

a channel region provided over a substrate and between a source region and a drain region;

a gate electrode provided over said substrate and provided adjacent to said channel region with a gate insulating film between said gate electrode and said channel region;

a first insulating film comprising silicon nitride provided over said channel region and said source region and said drain region and said gate electrode and said gate insulating film;

a second insulating film provided over said first insulating film and comprising polyamide to provide a first leveled surface over said first insulating film;

a drain electrode connected with said drain region and provided over said second insulating film;

a source electrode connected with said source region and provided over said second insulating film;

a third insulating film provided over said drain electrode and said source electrode and comprising polyimide to provide a second leveled surface over said drain electrode and said source electrode;

a black matrix provided over said third insulating film;

a fourth insulating film provided over said black matrix and comprising polyimide to provide a third leveled surface over said black matrix; and

a pixel electrode connected with one of said drain electrode and said source electrode and provided over said fourth insulating film.

2. (Original) A device according to claim 1 wherein said channel region and said source region and said drain region are provided in a semiconductor film comprising a plurality of radial crystal grains of silicon.

3. (Original) A device according to claim 2 wherein said semiconductor film has a thickness of 100 to 750 Å.

4. (Original) A device according to claim 1 wherein said semiconductor device is incorporated into one selected from the group consisting of a portable intelligent terminal, a head mounted display, a car navigational system, a mobile telephone, a portable video camera, and a projection display.

5. (Original) A device according to claim 1 wherein said semiconductor device is incorporated into a liquid crystal display.

6. (Original) A device according to claim 1 wherein said semiconductor device is incorporated into an electroluminescent display.

7. (Currently Amended) A semiconductor device comprising:
a channel region provided over a substrate and between a source region and a drain region;
a gate electrode provided over said substrate and provided adjacent to said channel region with a gate insulating film between said gate electrode and said channel region;

a first insulating film comprising silicon nitride provided over said channel region and said source region and said drain region and said gate electrode and said gate insulating film;

a second insulating film provided over said first insulating film and comprising polyimide to provide a first leveled surface over said first insulating film;

a drain electrode connected with said drain region and provided over said second insulating film;

a source electrode connected with said source region and provided over said second insulating film;

a third insulating film provided over said drain electrode and said source electrode and comprising polyimide to provide a second leveled surface over said drain electrode and said source electrode;

a black matrix provided over said third insulating film;

a fourth insulating film provided over said black matrix and comprising polyimide to provide a third leveled surface over said black matrix; and

a pixel electrode connected with one of said drain electrode and said source electrode and provided over said fourth insulating film, and

wherein said black matrix is in contact with said one of said drain electrode and said source electrode in a region in which said black matrix and said pixel electrode are overlapped with each other.

8. (Original) A device according to claim 7 wherein said channel region and said source region and said drain region are provided in a semiconductor film comprising a plurality of radial crystal grains of silicon.

9. (Original) A device according to claim 8 wherein said semiconductor film has a thickness of 100 to 750 Å.

10. (Original) A device according to claim 7 wherein said semiconductor device is incorporated into one selected from the group consisting of a portable intelligent terminal, a head mounted display, a car navigational system, a mobile telephone, a portable video camera, and a projection display.

11. (Original) A device according to claim 7 wherein said semiconductor device is incorporated into a liquid crystal display.

12. (Original) A device according to claim 7 wherein said semiconductor device is incorporated into an electroluminescent display.

13. (Currently Amended) A semiconductor device comprising:

a channel region provided over a substrate and between a source region and a drain region;

a gate electrode provided over said substrate and provided adjacent to said channel region with a gate insulating film between said gate electrode and said channel region;

a first insulating film comprising silicon nitride provided over said channel region and said source region and said drain region and said gate electrode and said gate insulating film;

a second insulating film provided over said first insulating film and comprising polyimide to provide a first leveled surface over said first insulating film;

a drain electrode connected with said drain region and provided over said second insulating film;

a source electrode connected with said source region and provided over said second insulating film;

a third insulating film provided over said drain electrode and said source electrode and comprising polyimide to provide a second leveled surface over said drain electrode and said source electrode;

a black matrix provided over said third insulating film;

a fourth insulating film provided over said black matrix and comprising polyimide to provide a third leveled surface over said black matrix; and

a pixel electrode connected with one of said drain electrode and said source electrode and provided over said fourth insulating film,

~~wherein at least a part of said black matrix is in contact with at least a part of said one of said drain electrode and said source electrode, and~~

wherein said black matrix is in contact with said one of said drain electrode and said source electrode in a region in which said black matrix and said pixel electrode are overlapped with each other.

14. (Original) A device according to claim 13 wherein said channel region and said source region and said drain region are provided in a semiconductor film comprising a plurality of radial crystal grains of silicon.

15. (Original) A device according to claim 14 wherein said semiconductor film has a thickness of 100 to 750 Å.

16. (Original) A device according to claim 13 wherein said semiconductor device is incorporated into one selected from the group consisting of a portable intelligent terminal, a head mounted display, a car navigational system, a mobile telephone, a portable video camera, and a projection display.

17. (Original) A device according to claim 13 wherein said semiconductor device is incorporated into a liquid crystal display.

18. (Original) A device according to claim 13 wherein said semiconductor device is incorporated into an electroluminescent display.

19. (Previously Presented) A semiconductor device comprising:

a channel region provided over a substrate and between a source region and a drain region;

a gate electrode provided over said substrate and provided adjacent to said channel region with a gate insulating film between said gate electrode and said channel region;

a first insulating film comprising silicon nitride provided over said channel region and said source region and said drain region and said gate electrode and said gate insulating film;

a second insulating film provided over said first insulating film and comprising polyamide to provide a first leveled surface over said first insulating film;

a drain electrode connected with said drain region and provided over said second insulating film;

a source electrode connected with said source region and provided over said second insulating film;

a third insulating film provided over said drain electrode and said source electrode and comprising polyimide to provide a second leveled surface over said drain electrode and said source electrode;

a black matrix provided over said third insulating film;

a fourth insulating film provided over said black matrix and comprising polyimide to provide a third leveled surface over said black matrix; and

a pixel electrode connected with one of said drain electrode and said source electrode and provided over said fourth insulating film,

wherein at least a part of said black matrix is in contact with at least a part of said one of said drain electrode and said source electrode.

20. (Previously Presented) A device according to claim 19 wherein said channel region and said source region and said drain region are provided in a semiconductor film comprising a plurality of radial crystal grains of silicon.

21. (Previously Presented) A device according to claim 20 wherein said semiconductor film has a thickness of 100 to 750 Å.

22. (Previously Presented) A device according to claim 19 wherein said semiconductor device is incorporated into one selected from the group consisting of a portable intelligent terminal, a head mounted display, a car navigational system, a mobile telephone, a portable video camera, and a projection display.

23. (Previously Presented) A device according to claim 19 wherein said semiconductor device is incorporated into a liquid crystal display.

24. (Previously Presented) A device according to claim 19 wherein said semiconductor device is incorporated into an electroluminescent display.